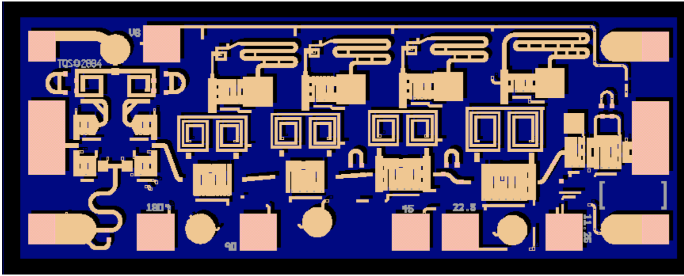
TriQuint SEMICONDUCTOR®

Advance Product Information
August 9, 2004

30 GHz 5-Bit Phase Shifter

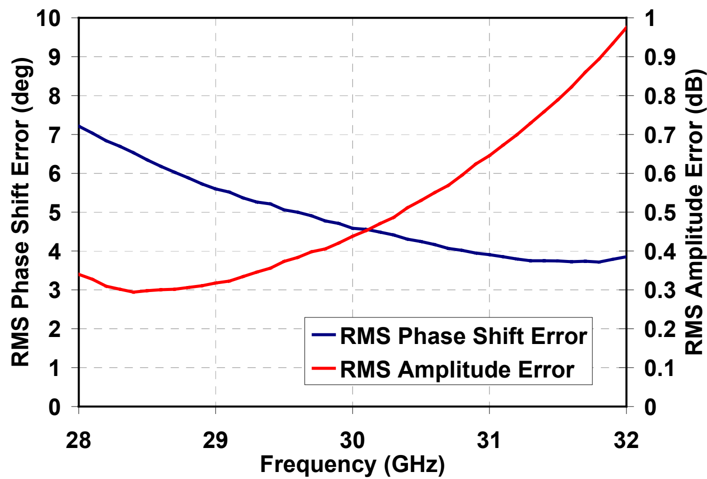
TGP2100-EPU

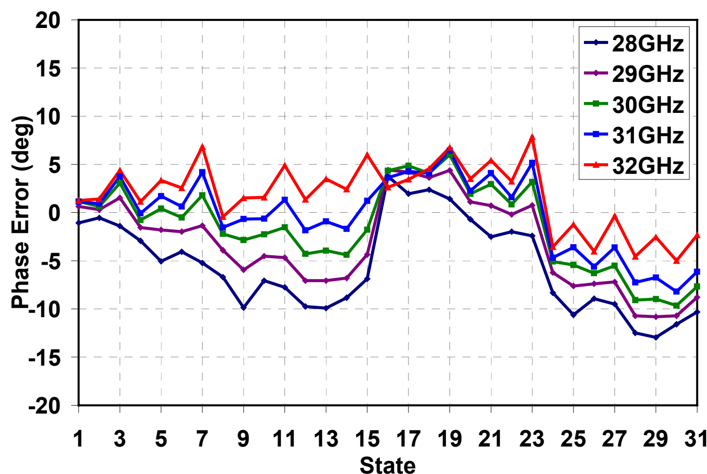


Key Features and Performance

- Positive Control Voltage
- Single-Ended Logic
- CMOS Compatible
- Frequency Range: 28 - 32 GHz
- 0.25µm pHEMT 3MI Technology
- Chip dimensions:
  1.88 x 0.75 x 0.1 mm
  (0.074 x 0.030 x 0.004 inches)

Preliminary Measured Performance





Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

TABLE I
MAXIMUM RATINGS

Symbol	Parameter	Value	Notes
V_C	Control Voltage Range	0 - +8 V	1/ 2/
I_D	Control Supply Current	1 mA	1/ 2/
P_{IN}	Input Continuous Wave Power	20 dBm	1/ 2/
P_D	Power Dissipation	0.1 W	1/ 2/
T_{CH}	Operating Channel Temperature	150 ^{0}C	3/
T_M	Mounting Temperature (30 Seconds)	320 ^{0}C	
T_{STG}	Storage Temperature	-65 to 150 ^{0}C	

1/ These ratings represent the maximum operable values for this device

2/ Combinations of supply voltage, supply current, input power, and output power shall not exceed P_D at a package base temperature of 70°C

3/ Junction operating temperature will directly affect the device median time to failure (MTTF). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

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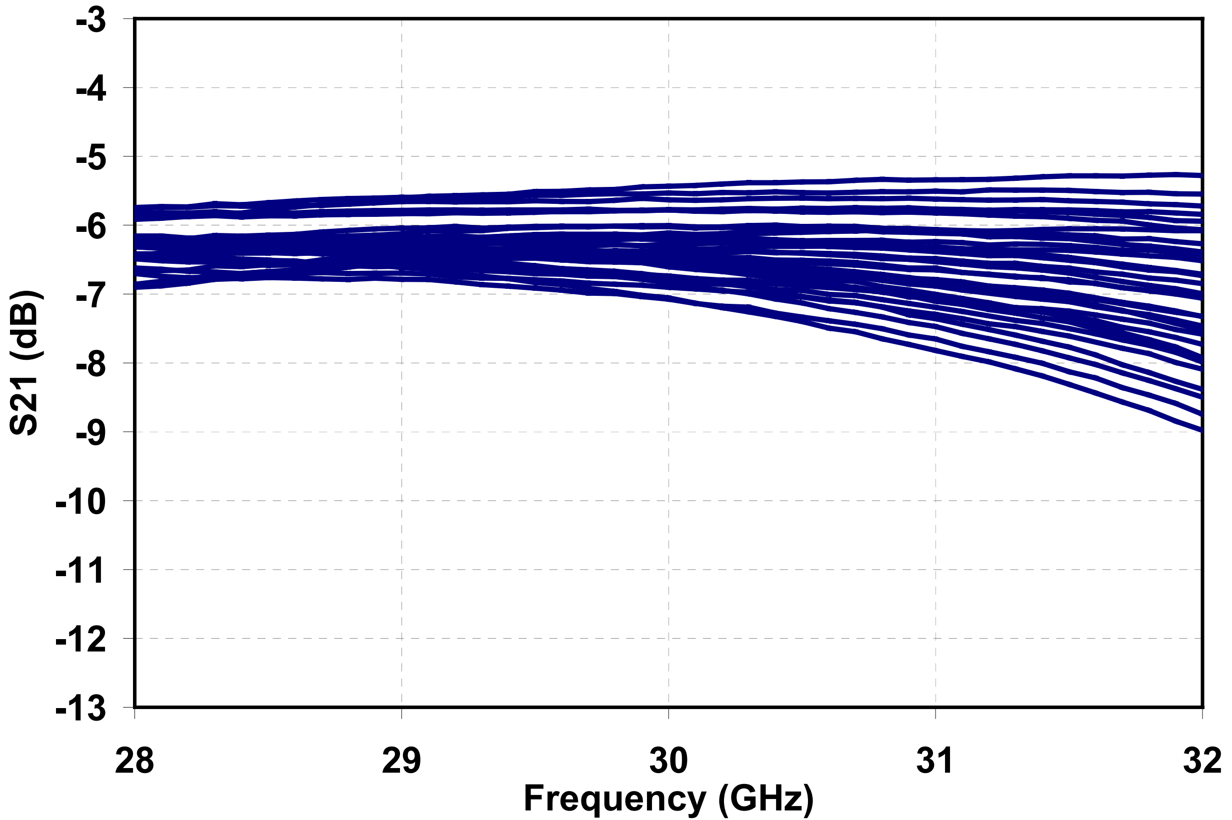
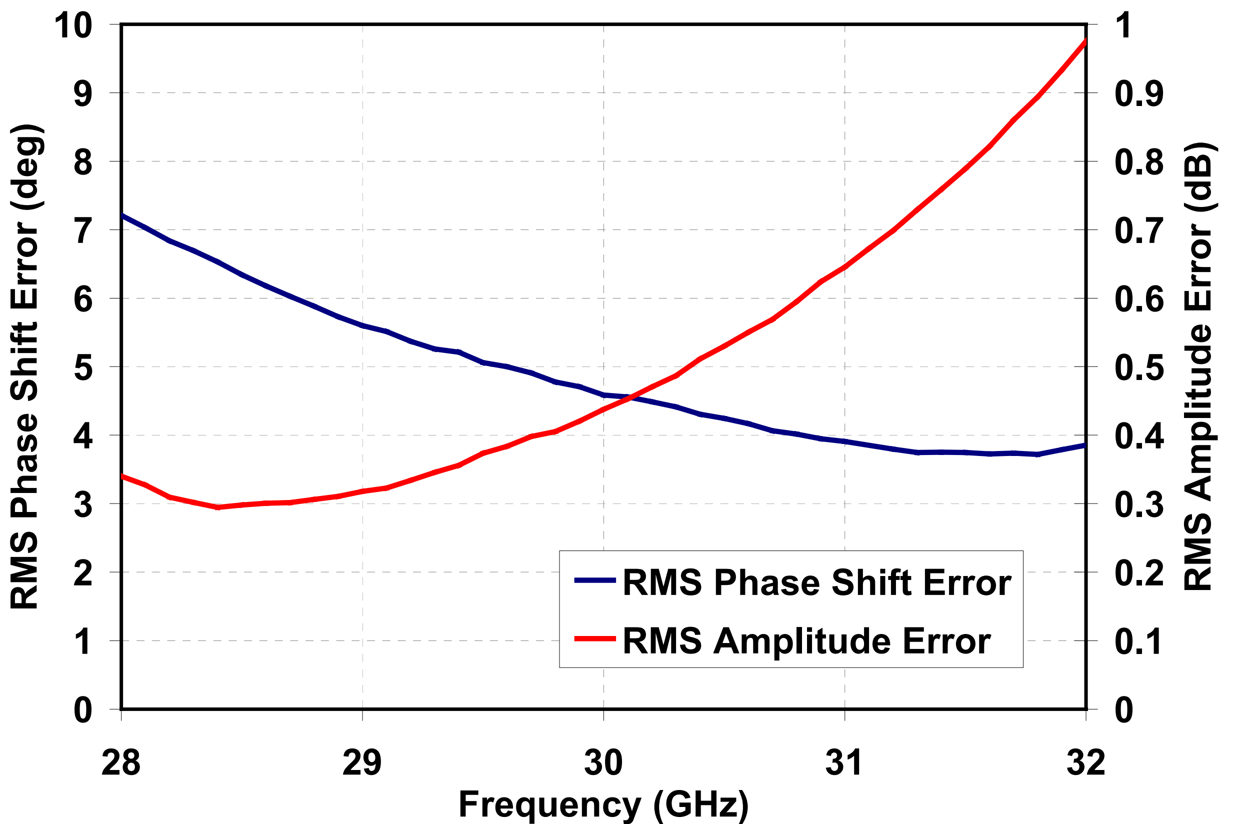
Preliminary Measured Data





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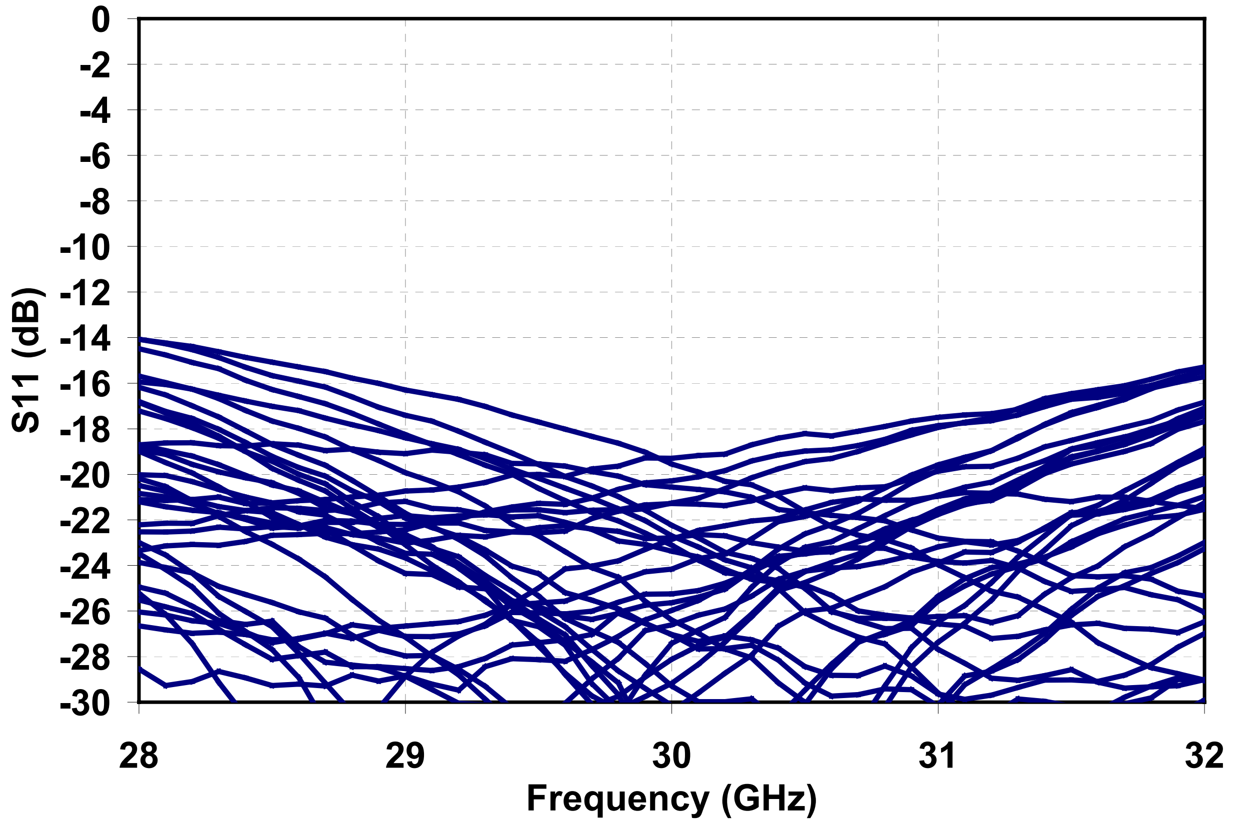

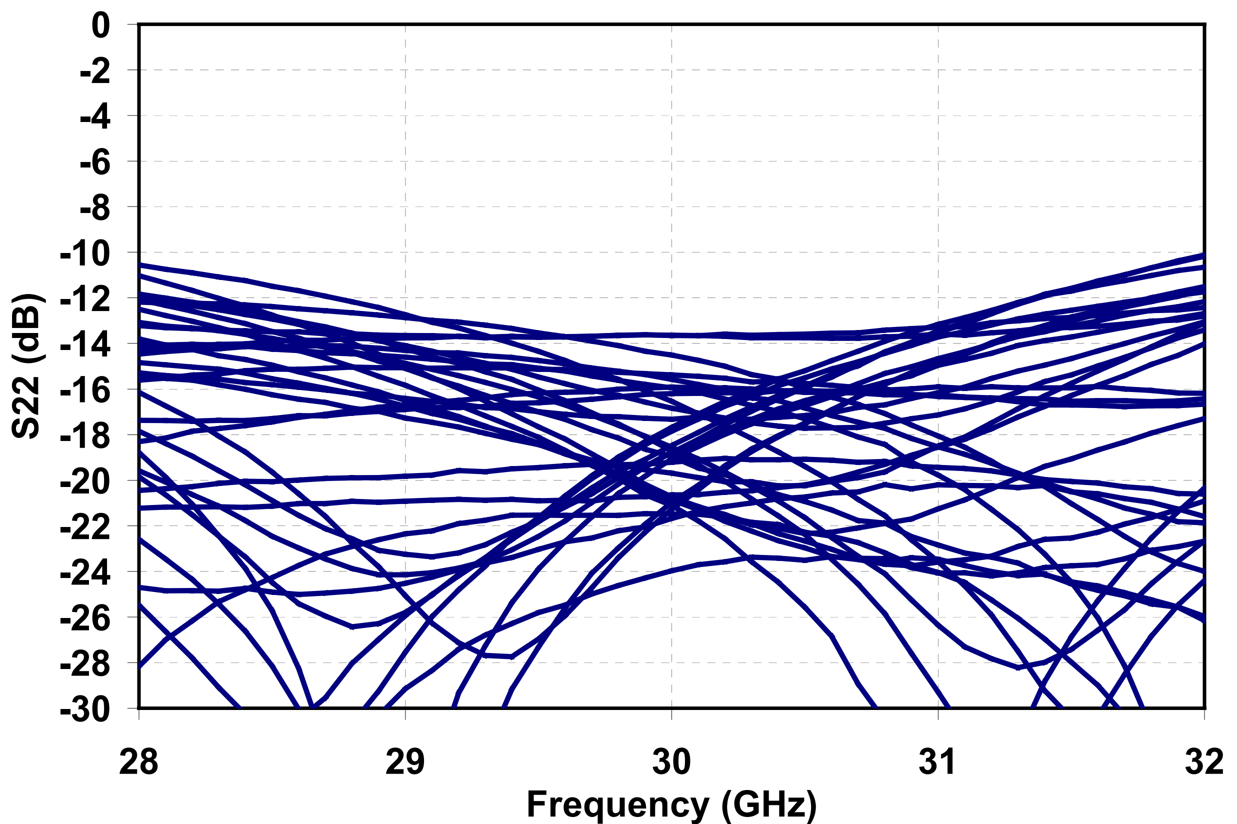

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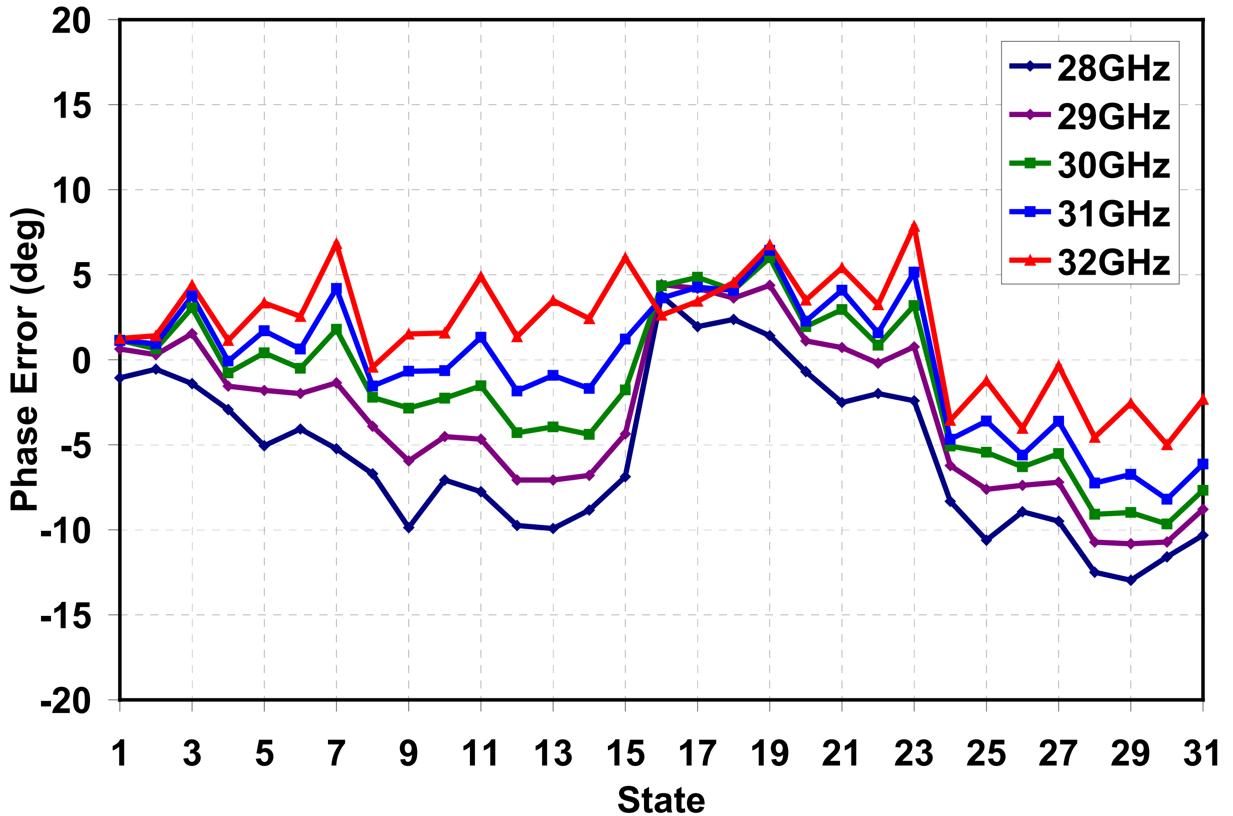

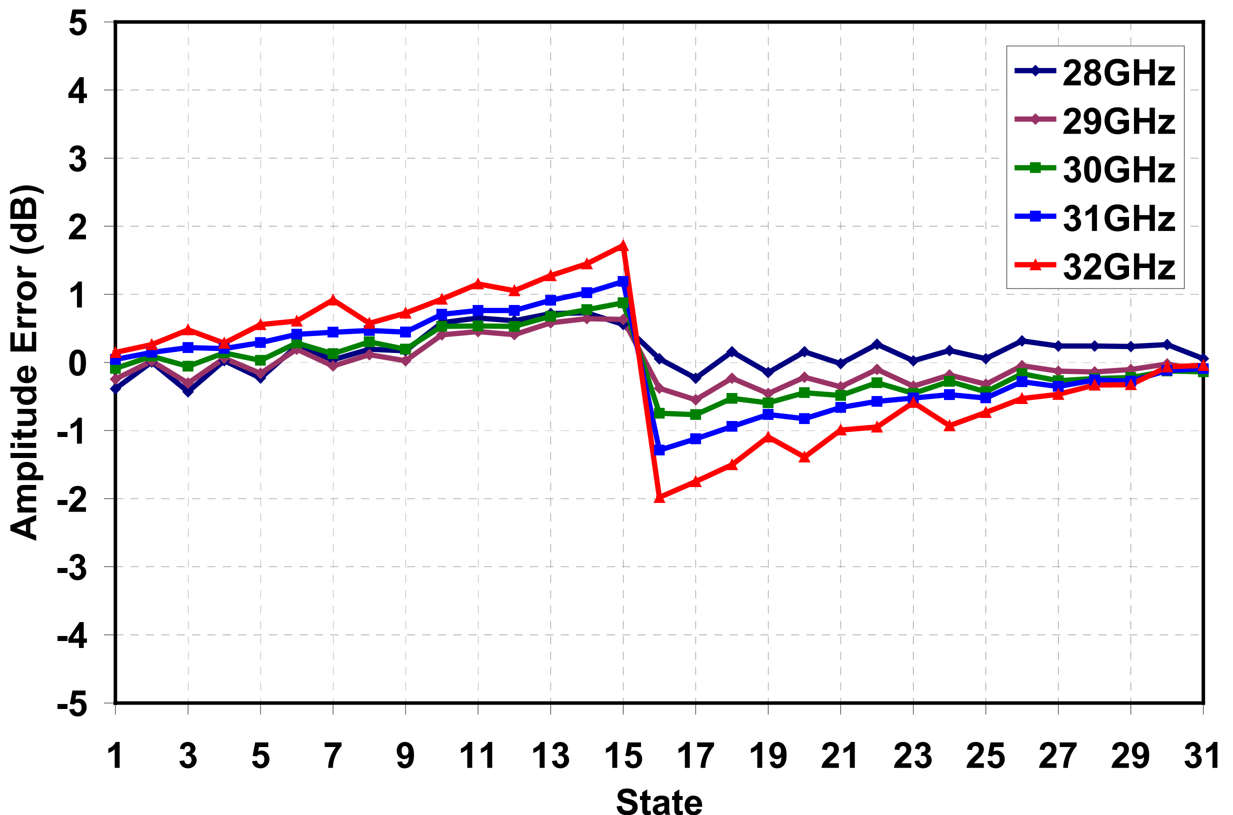

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State Table

State	V-Supply	V-11.25	V-22.5	V-45	V-90	V-180	Phase Shift
0	+5V	0V	0V	0V	0V	0V	Reference
1	+5V	+5V	0V	0V	0V	0V	11.25°
2	+5V	0V	+5V	0V	0V	0V	22.5°
3	+5V	+5V	+5V	0V	0V	0V	33.75°
4	+5V	0V	0V	+5V	0V	0V	45°
5	+5V	+5V	0V	+5V	0V	0V	56.25°
6	+5V	0V	+5V	+5V	0V	0V	67.5°
7	+5V	+5V	+5V	+5V	0V	0V	78.75°
8	+5V	0V	0V	0V	+5V	0V	90°
9	+5V	+5V	0V	0V	+5V	0V	101.25°
10	+5V	0V	+5V	0V	+5V	0V	112.5°
11	+5V	+5V	+5V	0V	+5V	0V	123.75°
12	+5V	0V	0V	+5V	+5V	0V	135°
13	+5V	+5V	0V	+5V	+5V	0V	146.25°
14	+5V	0V	+5V	+5V	+5V	0V	157.5°
15	+5V	+5V	+5V	+5V	+5V	0V	168.75°
16	+5V	0V	0V	0V	0V	+5V	180°
17	+5V	+5V	0V	0V	0V	+5V	191.25°
18	+5V	0V	+5V	0V	0V	+5V	202.5°
19	+5V	+5V	+5V	0V	0V	+5V	213.75°
20	+5V	0V	0V	+5V	0V	+5V	225°
21	+5V	+5V	0V	+5V	0V	+5V	236.25°
22	+5V	0V	+5V	+5V	0V	+5V	247.5°
23	+5V	+5V	+5V	+5V	0V	+5V	258.75°
24	+5V	0V	0V	0V	+5V	+5V	270°
25	+5V	+5V	0V	0V	+5V	+5V	281.25°
26	+5V	0V	+5V	0V	+5V	+5V	292.5°
27	+5V	+5V	+5V	0V	+5V	+5V	303.75°
28	+5V	0V	0V	+5V	+5V	+5V	315°
29	+5V	+5V	0V	+5V	+5V	+5V	326.25°
30	+5V	0V	+5V	+5V	+5V	+5V	337.5°
31	+5V	+5V	+5V	+5V	+5V	+5V	348.75°

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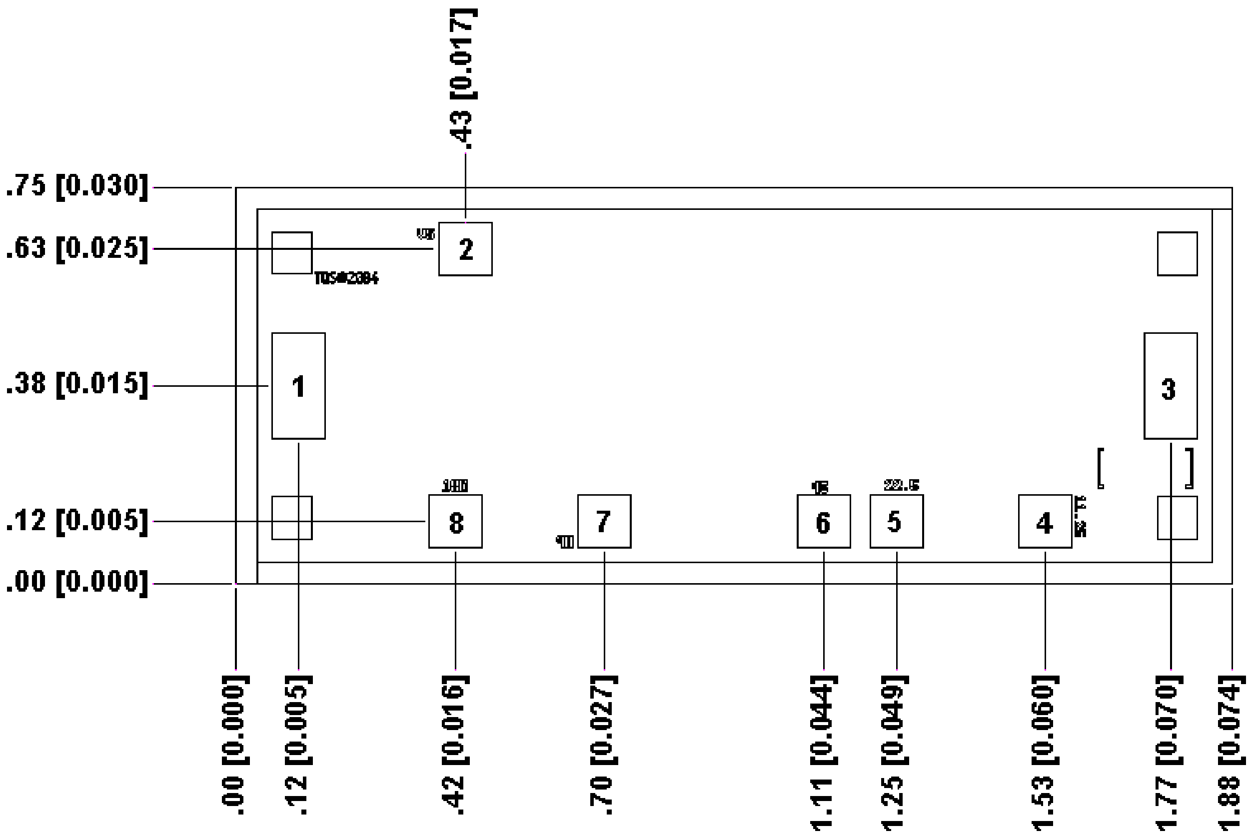
Mechanical Drawing



Units: millimeters [inches]
Thickness: 0.10 [0.004] (reference only)
Chip edge to bond pad dimensions are shown to center of bond pads.
Chip size tolerance: ±0.05 [0.002]
RF ground through backside

Bond Pad #1	**RF Input**	**0.10 x 0.20**	**[0.004 x 0.008]**
Bond Pad #2	**V-Supply (+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**
Bond Pad #3	**RF Output**	**0.10 x 0.20**	**[0.004 x 0.008]**
Bond Pad #4	**V-11.25 (ON V=+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**
Bond Pad #5	**V-22.5 (ON V=+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**
Bond Pad #6	**V-45 (ON V=+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**
Bond Pad #7	**V-90 (ON V=+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**
Bond Pad #8	**V-180 (ON V=+5V)**	**0.10 x 0.10**	**[0.004 x 0.004]**

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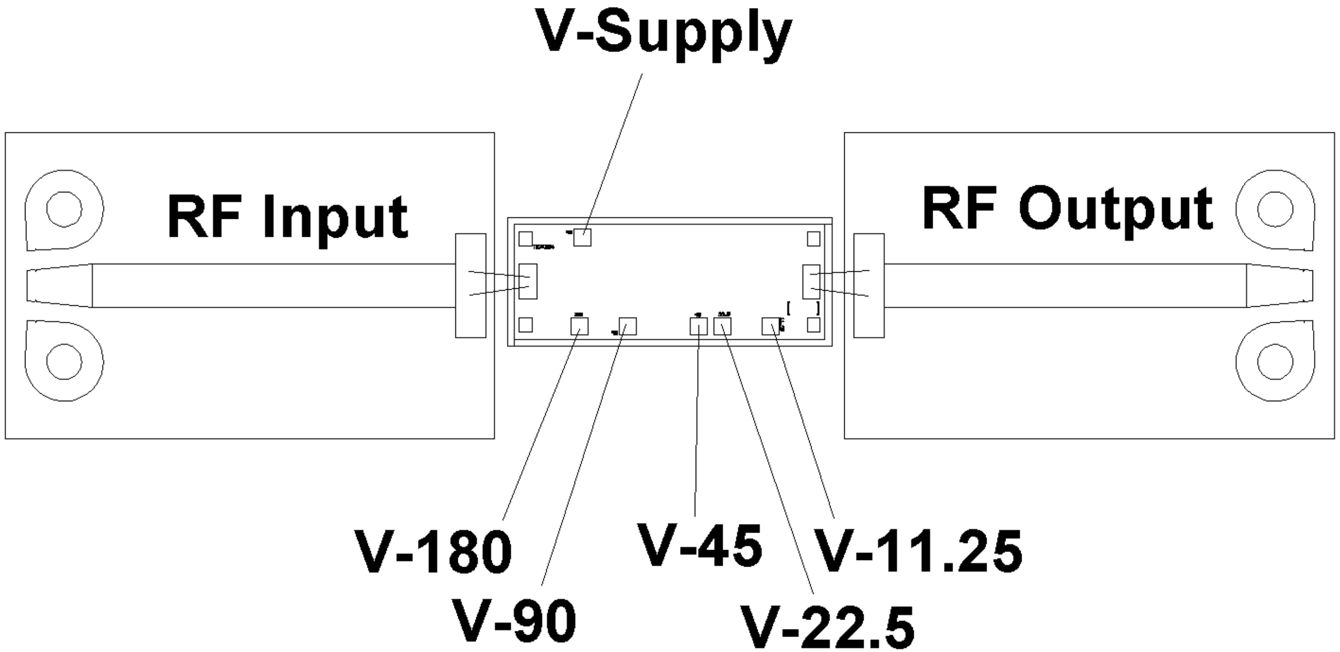
Chip Assembly & Bonding Diagram



Devices were tested with 500Ω resistors in series with control lines

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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Assembly Process Notes

Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C. (30 seconds maximum)
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Maximum stage temperature is 200°C.

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